



## **SKiiP® power modules**

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- SKiiP - Introduction
- SKiiP Technology
- SKiiP – Technical Details
- SKiiP – Logistical Details

# SKiiP

# Introduction

# Power semiconductors

Discrete

Modules

Systems

IGBT

MOSFET

Thyristor

Diode

CIB

SEMITOP

MiniSKiiP

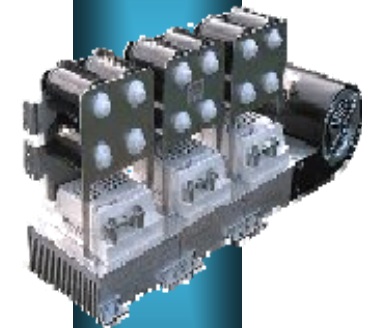
SEMI-TRANS

SEMIx

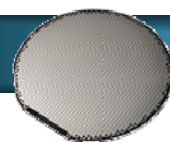
SKiM

SKiiP 2, 3

SEMI-STACK



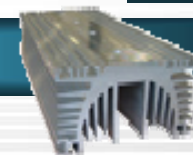
Chips



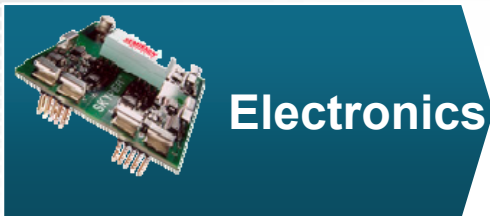
Driver



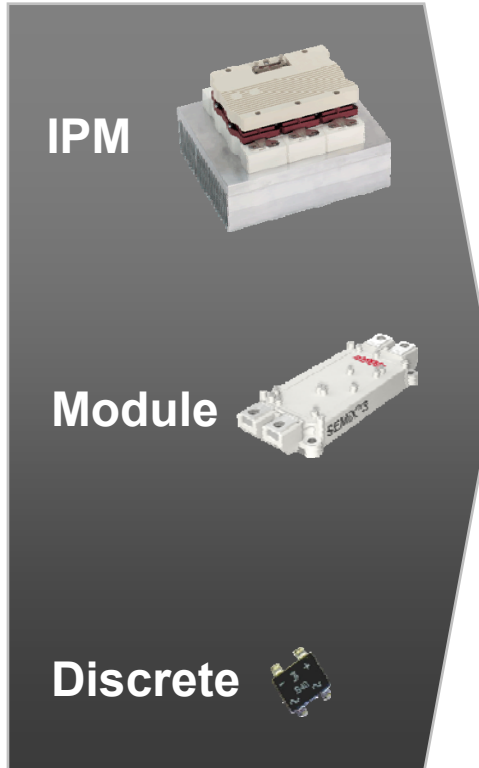
Heat sink



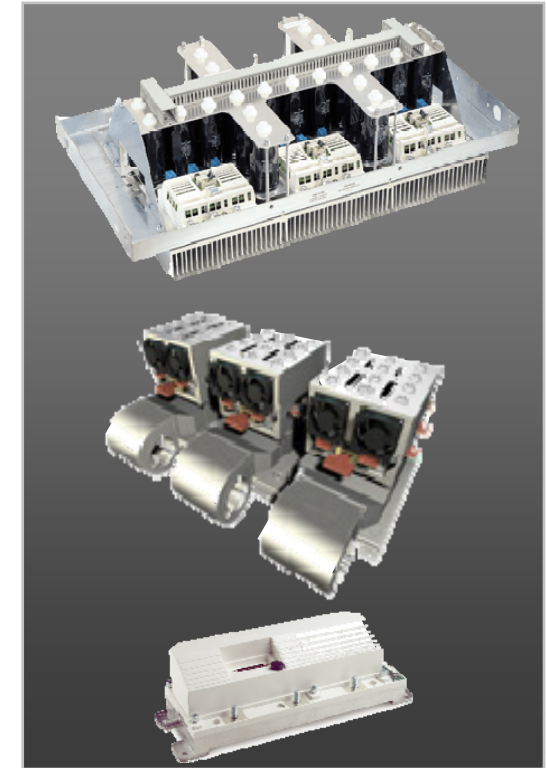
## Technologies



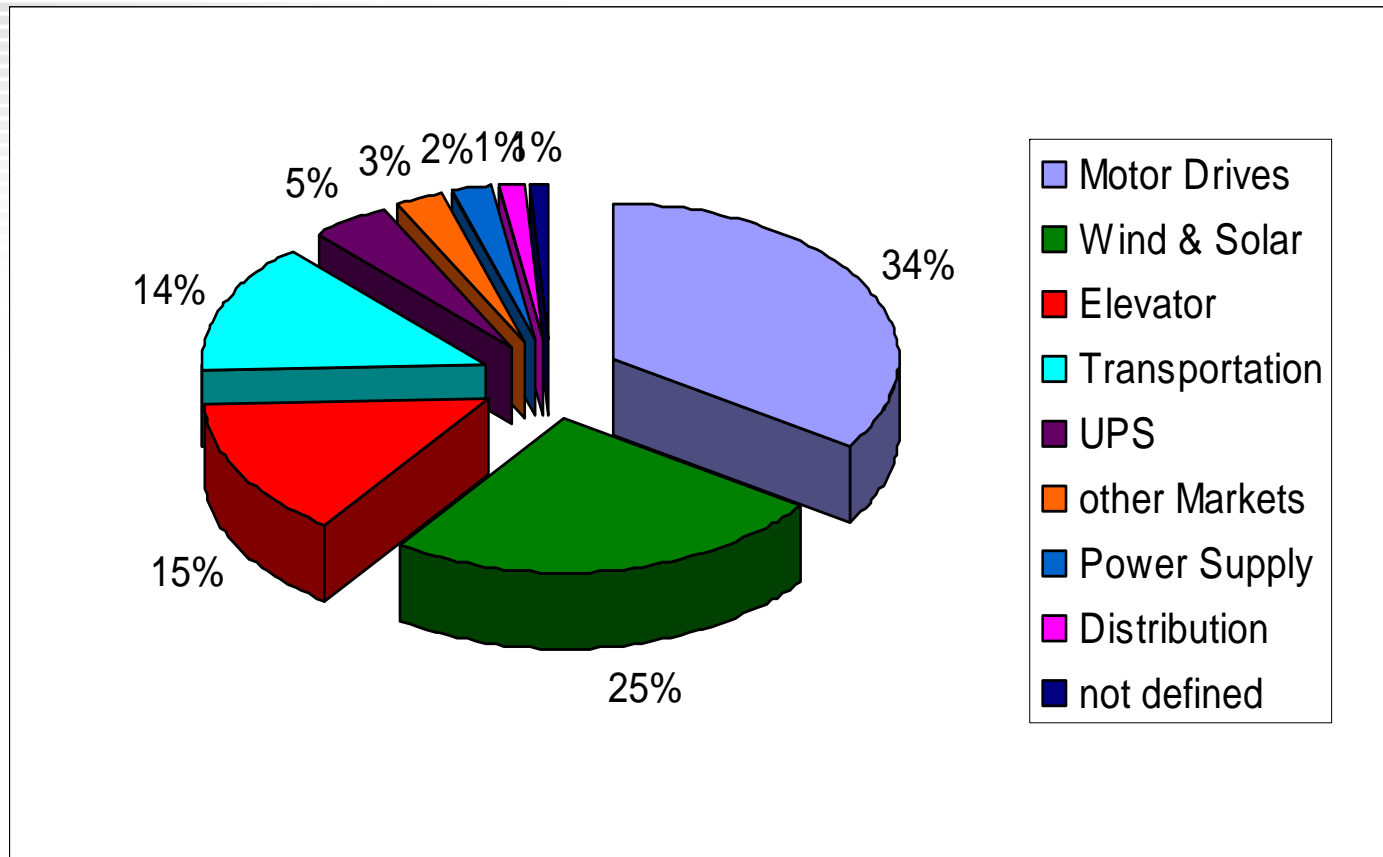
## Components



## Systems



# SKiiP markets



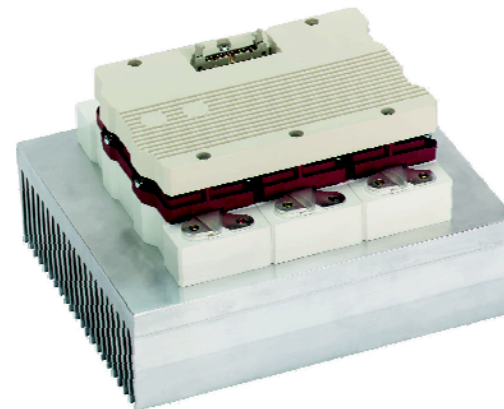
SKiiP: 20% of Semikron Germany turn over

## Features

- ▶ pure pressure contacted system
- ▶ integrated driver circuit and sensors
- ▶ cooling system

## Power Range

- ▶ **SKiiP® 2**
  - ▶ 150A - 1200A / 1200V, 1700V
  - ▶ Motor power range from 37kW to 500kW
  - ▶ Circuits: half bridge, 1-phase bridge, 3-phase-bridge, chopper
- ▶ **SKiiP® 3**
  - ▶ 300A - 2400A / 1200V, 1700V
  - ▶ Motor power range from 55kW to 750 kW
  - ▶ Circuits: half bridge (GB), 3-phase-bridge (GD)



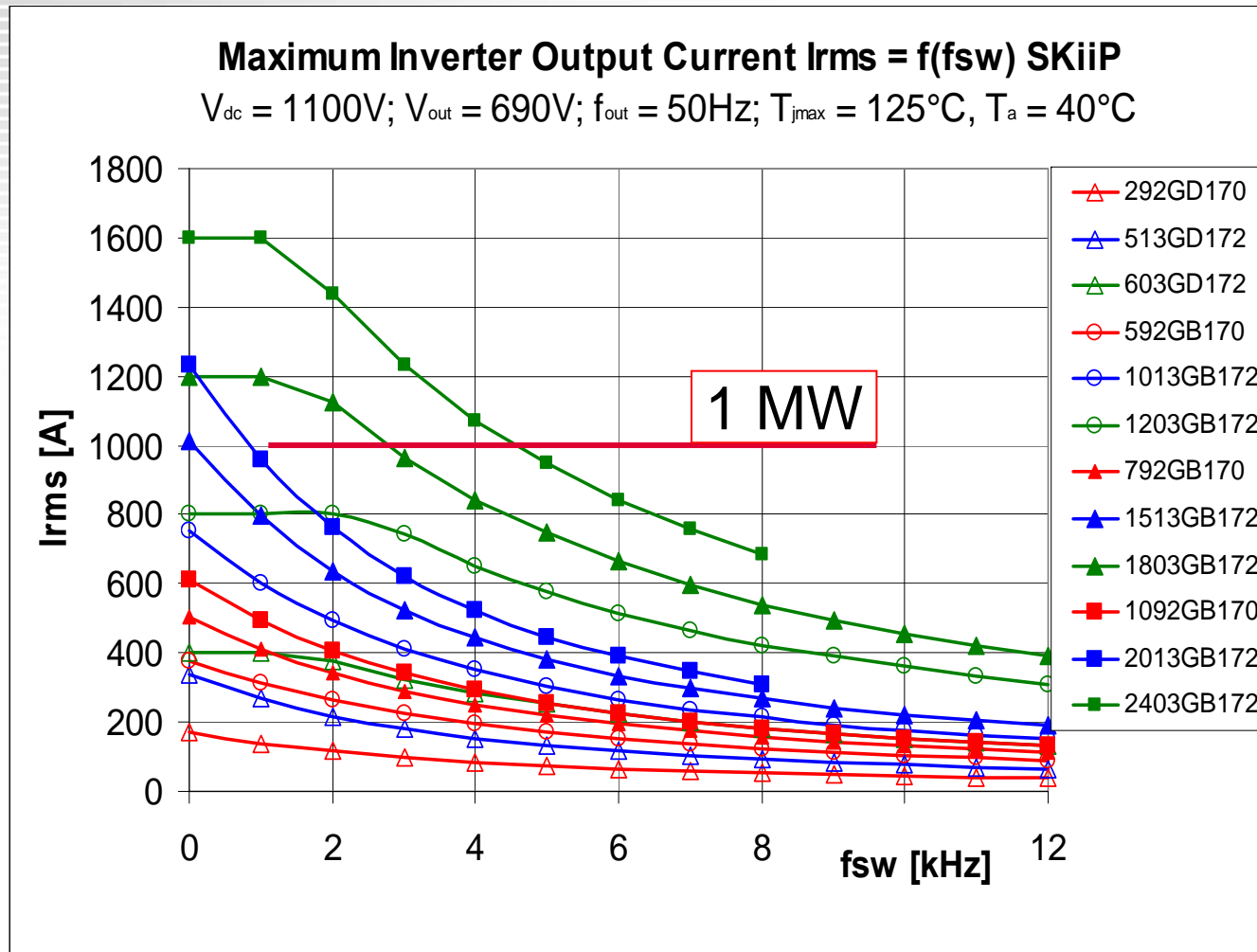
## ➤ SKiiP® Systems feature

- ▶ IGBT and CAL® diode power semiconductors assembled with SKiiP® technology
- ▶ Integrated gate driver
- ▶ Integrated sensors
- ▶ Integrated heat sink





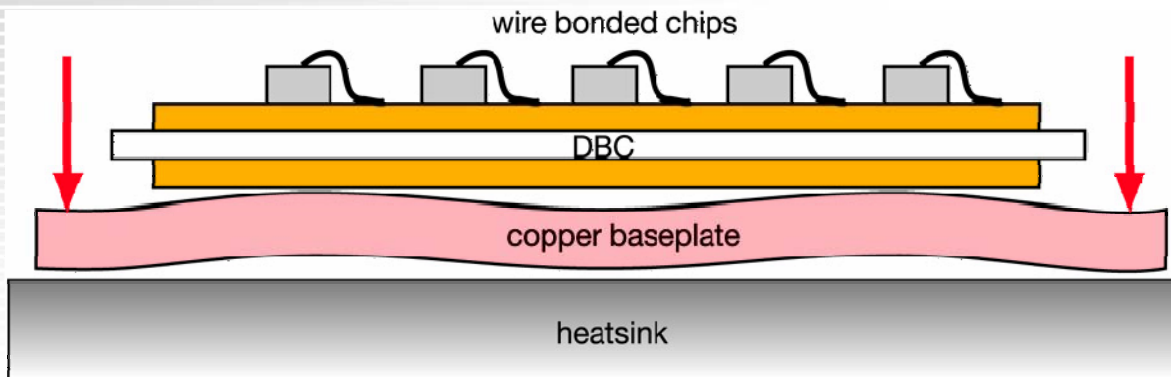
# Max. Power range overview (example 1700V SKiiP)



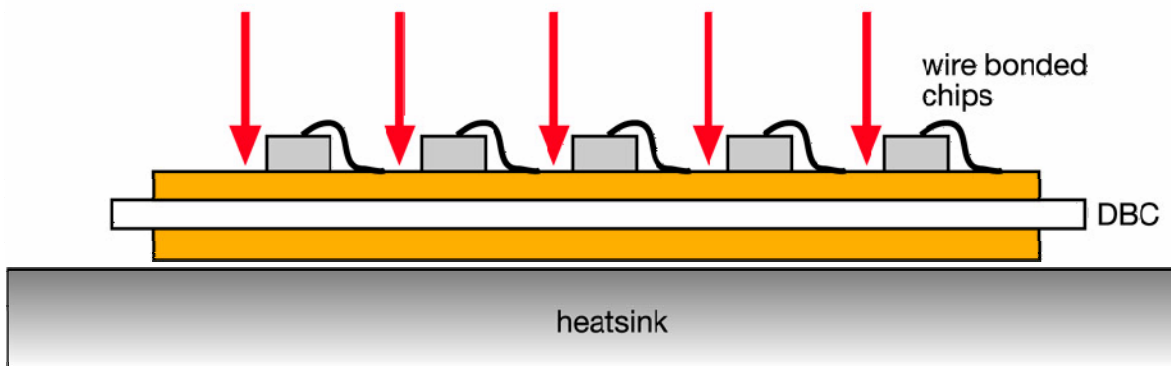
Green  
water-cooled SKiiP3  
Blue  
air-cooled SKiiP3  
Red  
air-cooled SKiiP2

# SKiiP Technology

# Comparison module with and without copper baseplate



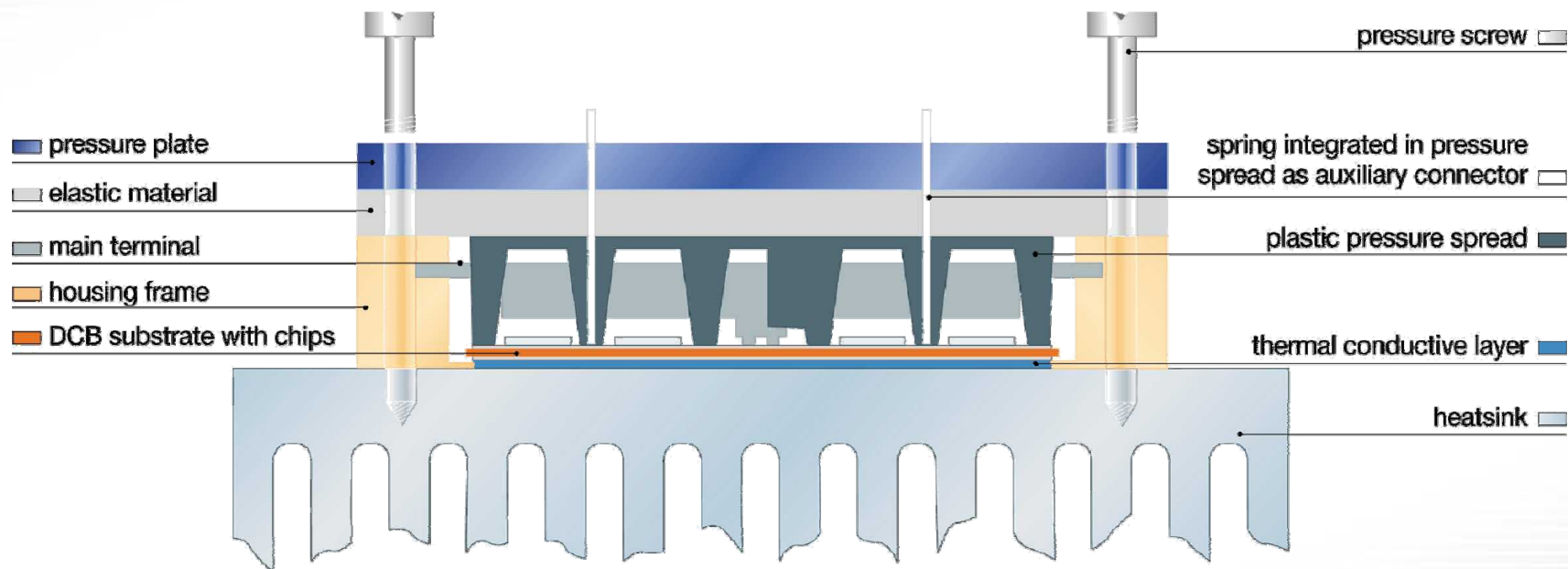
Baseplate mounted module expansion behavior at high temperatures



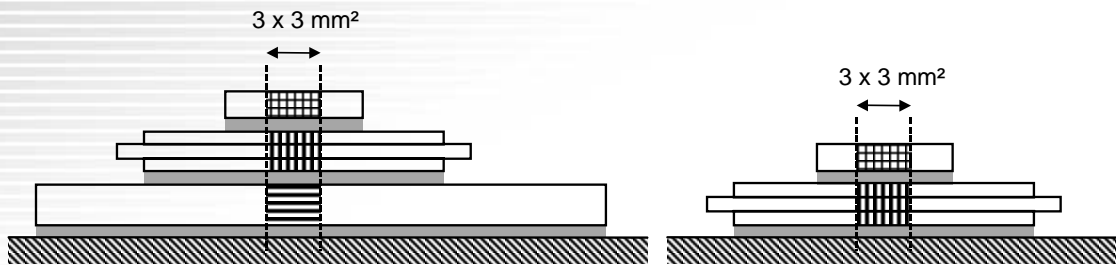
Distributed vertical pressure

# SKiiP<sup>®</sup> technology

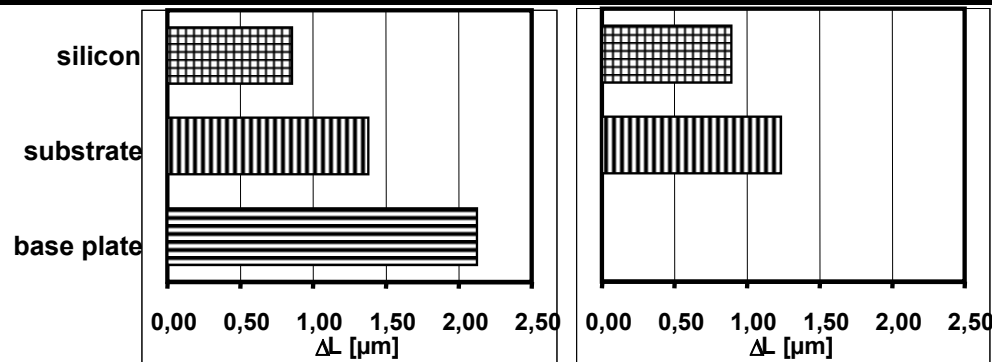
- ▶ base plate free power section
- ▶ inherent pressure contact technology for thermal and electrical contacts
- ▶ low stray inductance, homogenous current distribution



# Comparison: Match of thermal expansion Module - SKiiP® (AL<sub>2</sub>O<sub>3</sub> - substrate)











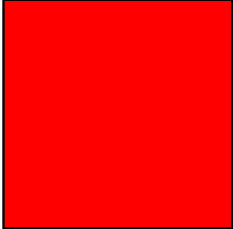
System:	standard 34mm module 0.38mm-Al <sub>2</sub> O <sub>3</sub> / Cu base plate			SKiiP pressure system 0.38mm-Al <sub>2</sub> O <sub>3</sub>		
Results:	T-T <sub>kk</sub> [K]	$\Delta L/L$ [1E-6/K]	$\Delta L$ [μm]	T-T <sub>kk</sub> [K]	$\Delta L/L$ [1E-6/K]	$\Delta L$ [μm]
silicon	69,7	4,1	0,86	62,6	4,1	0,77
substrate	55,4	8,3	1,38	48,3	7,8	1,13
base plate	40,5	17,5	2,13	—	—	—



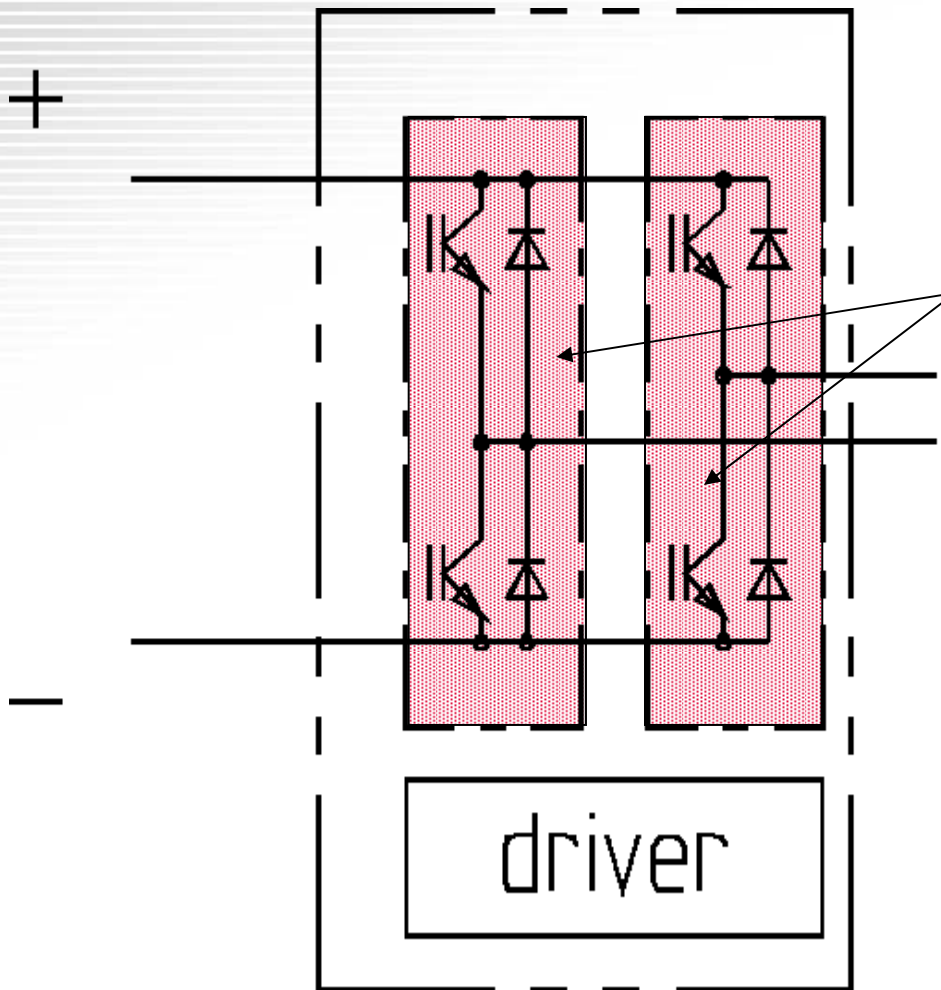
# thermal fatigue in power modules

R = characteristic figure for reliability risc considerations when two different materials are joined by soldering, brazing or welding

R = difference in CTE (Coefficient of Thermal Expansion) X length of mechanical contact

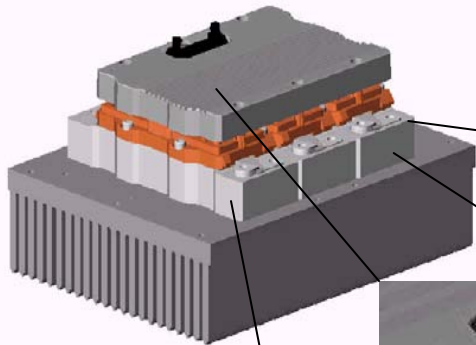
typical example	difference in CTE		length of contact		reliability risc R
wire bonding		X		=	
soldering of chip to substrate		X		=	
soldering of substrate to baseplate		X		=	

# guarantees low inductance in commutation circuit

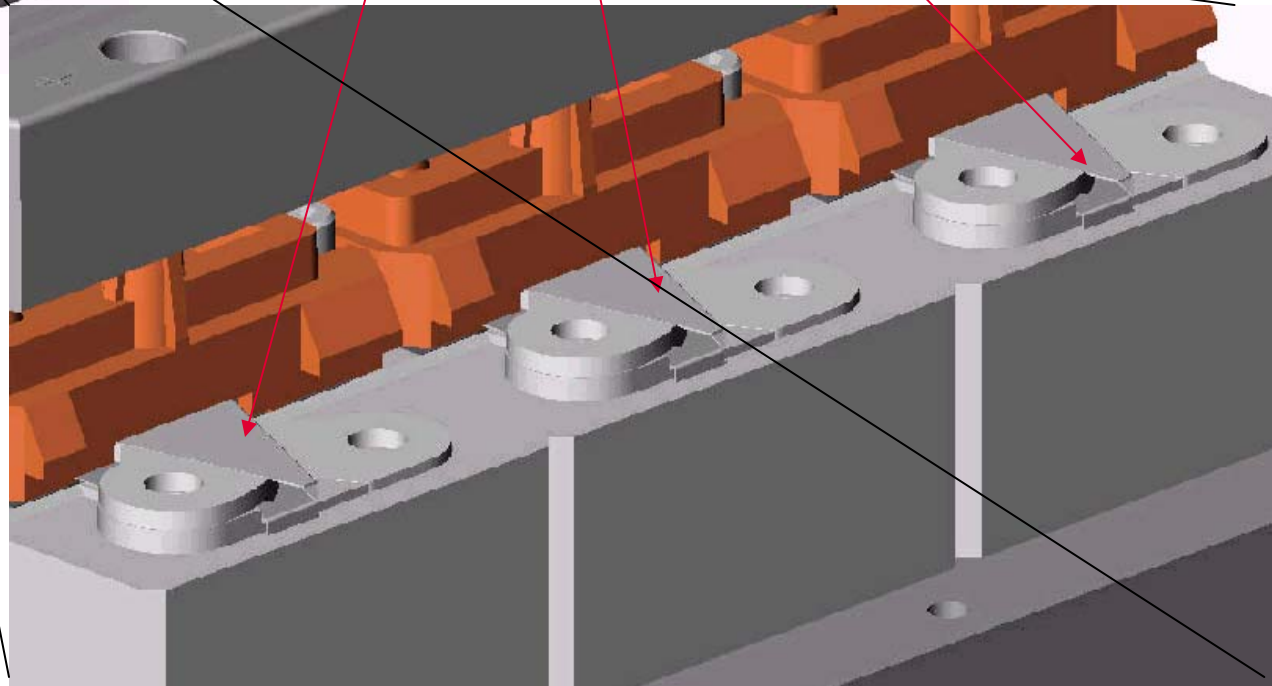


**Semiconductors of commutation circuit, i.e. TOP switch - BOTTOM diode  
BOTTOM switch - TOP diode, are integrated on one ceramic substrate:  
=> low inductance  
=> low voltage overshoot  
=> high utilisation of Vces**

# guarantees homogenous current distribution



Low inductive DC-link terminal  
=> low voltage overshoot during commutation  
=> homogenous current distribution





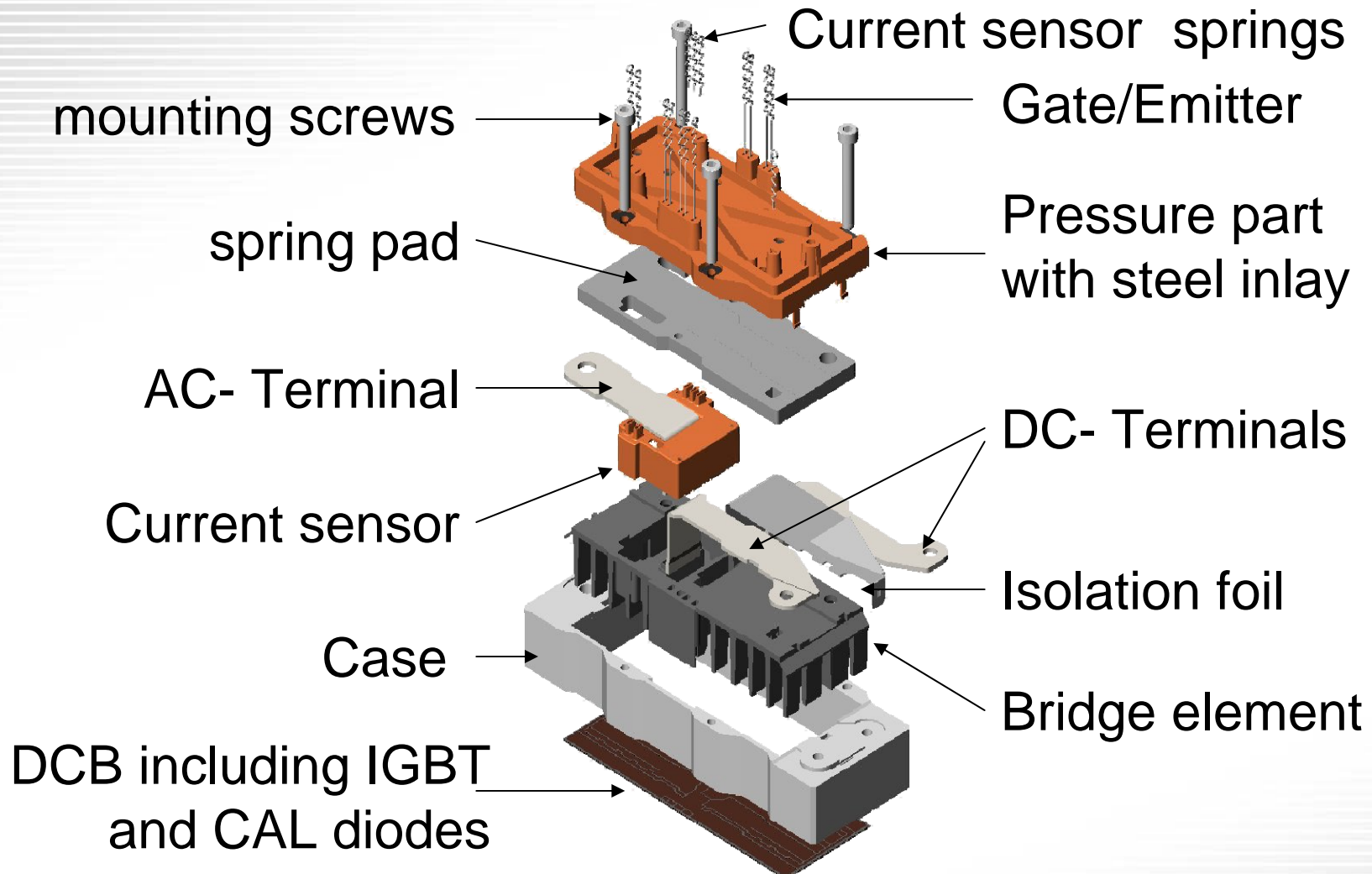
# Summary: Benefits of



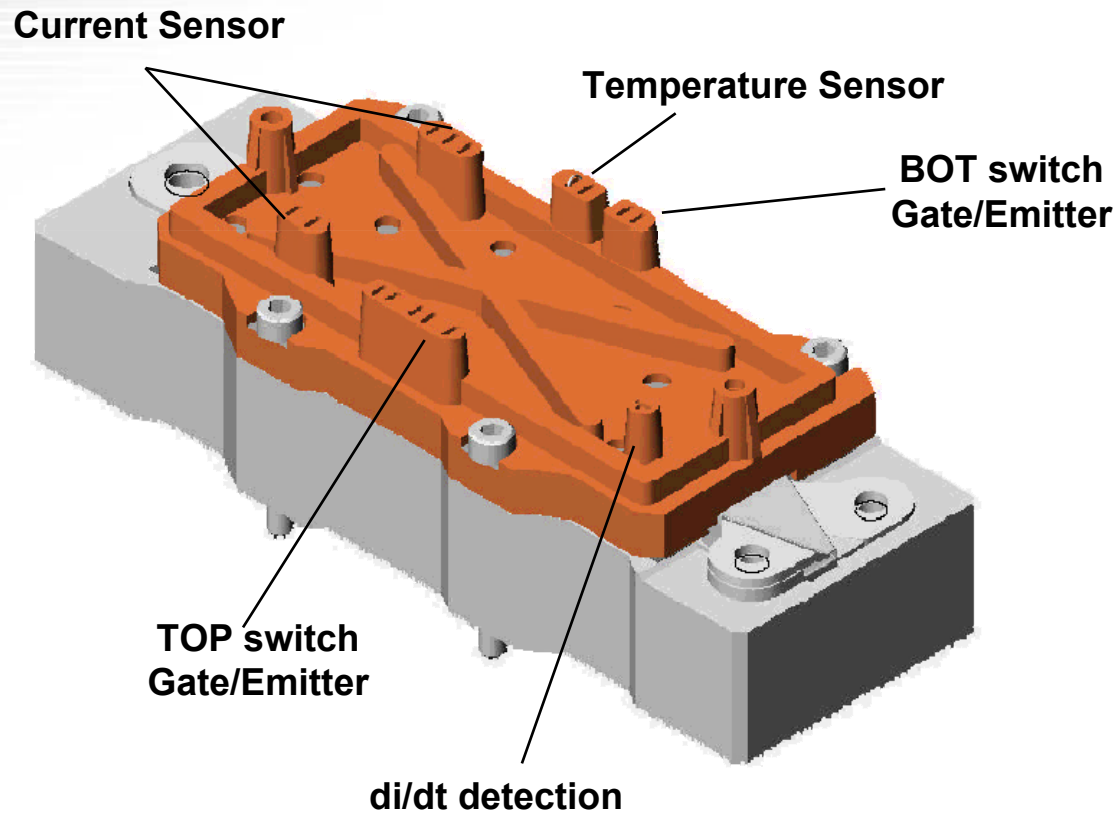
- ▶ **no solder ceramic to baseplate => no thermal fatigue => outstanding thermal cycling capability**
- ▶ **more homogenous contact module-heat sink => lower  $R_{thjh}$  => longer lifetime**
- ▶ **full utilization of high performance AlN ceramic => best cost/performance ratio**
- ▶ **multiple paralleled terminals => homogenous current distribution**
- ▶ **DC-terminals prepared for low inductive connection to DC-link => low voltage overshoot during commutation => high DC link voltage feasible, e.g. 900V for 1200V SKiiP**

# SKiiP - Technical Details

# Example: SKiiP<sup>®</sup> 3 power section assembly with

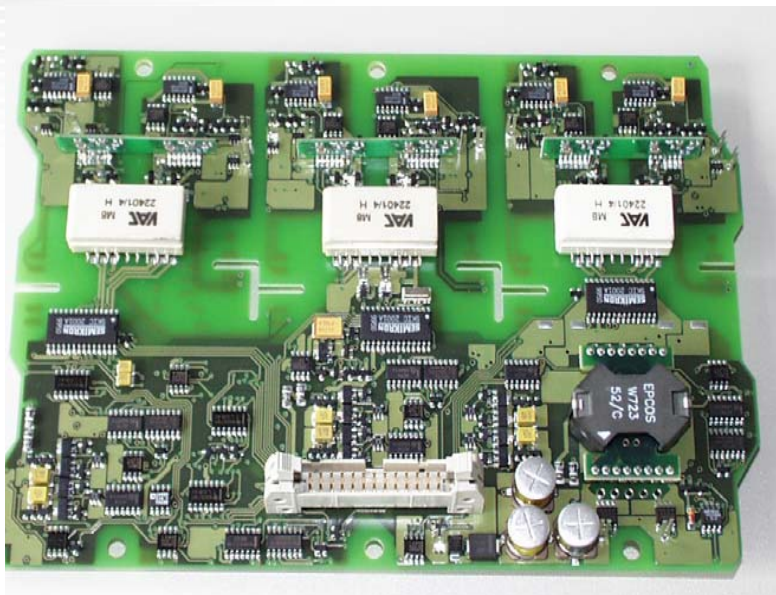


# Connection to driver

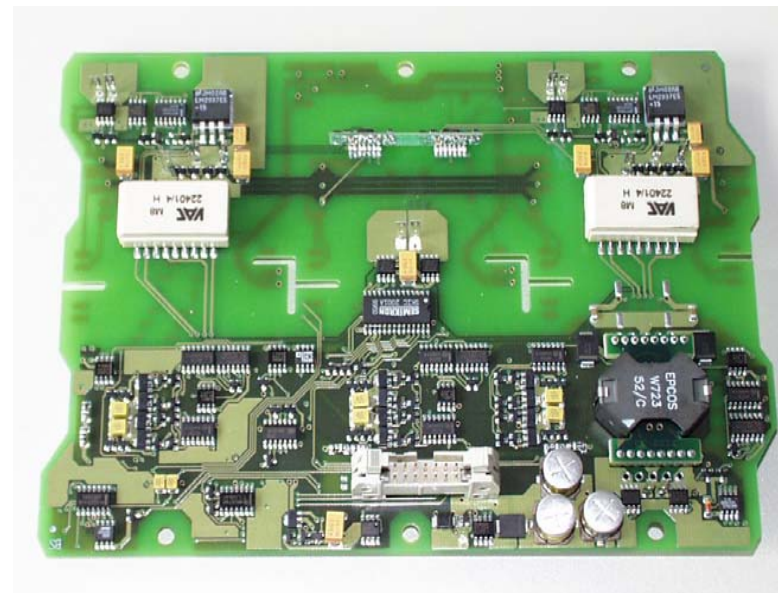


# SKiiP<sup>®</sup> 3 gate driver

(without cover and moulding)

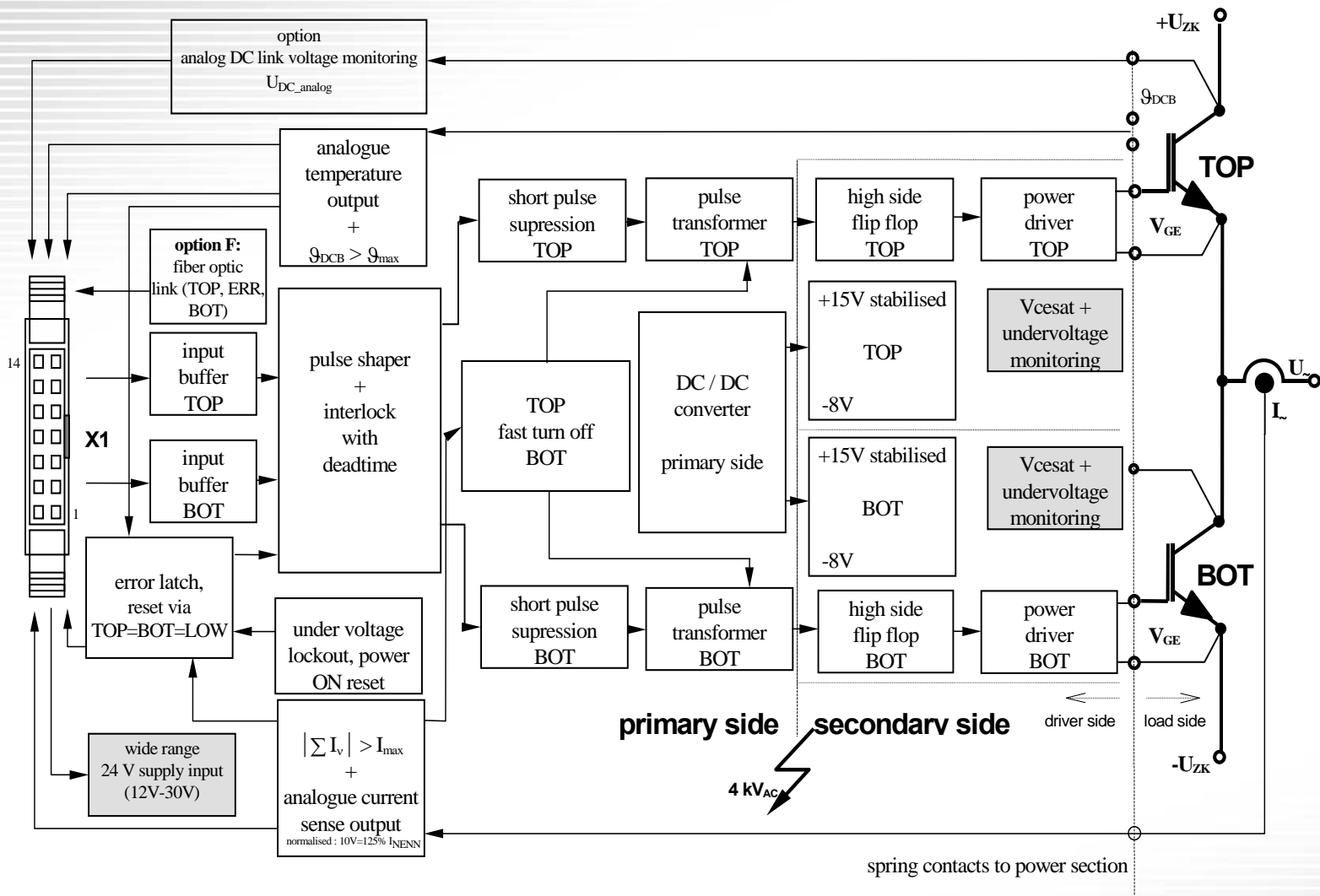


GD- Driver

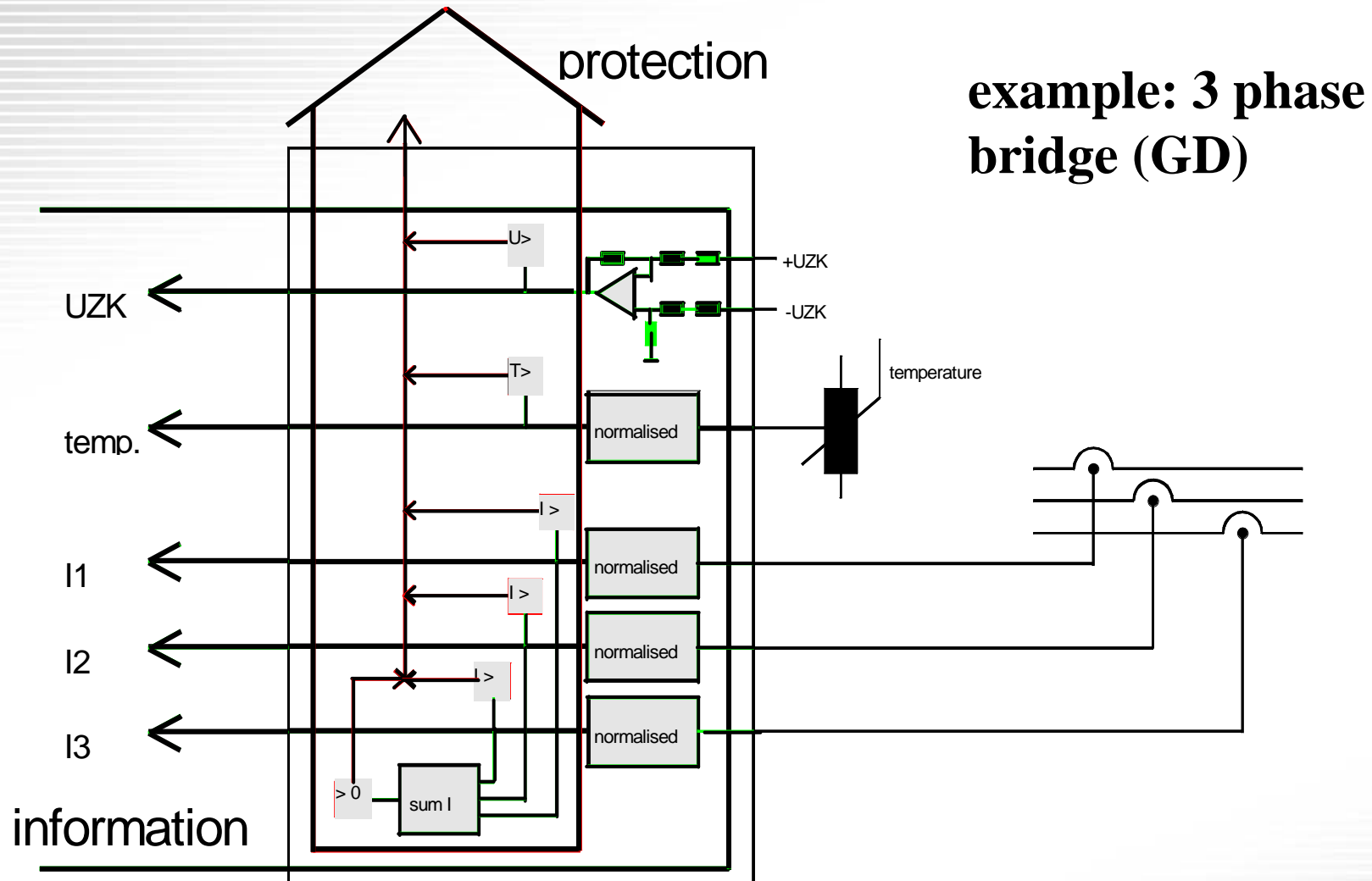


GB 3-fold Driver

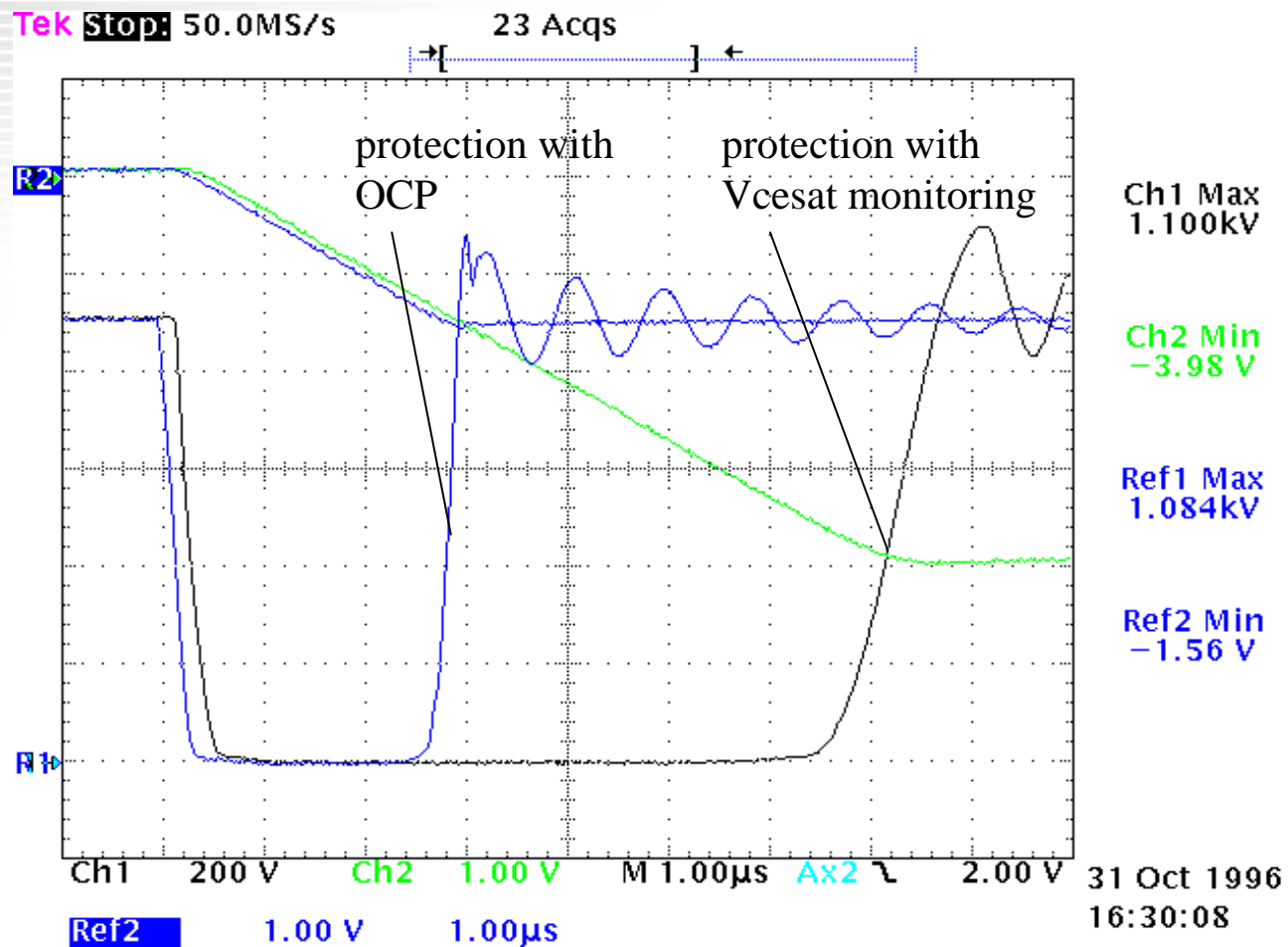
# SKiiP® System: Integrated gate driver example: block diagram dual gate drive



# Integrated functions for *protection and information*



# Protection comparison: $V_{CEsat}$ monitoring versus OCP

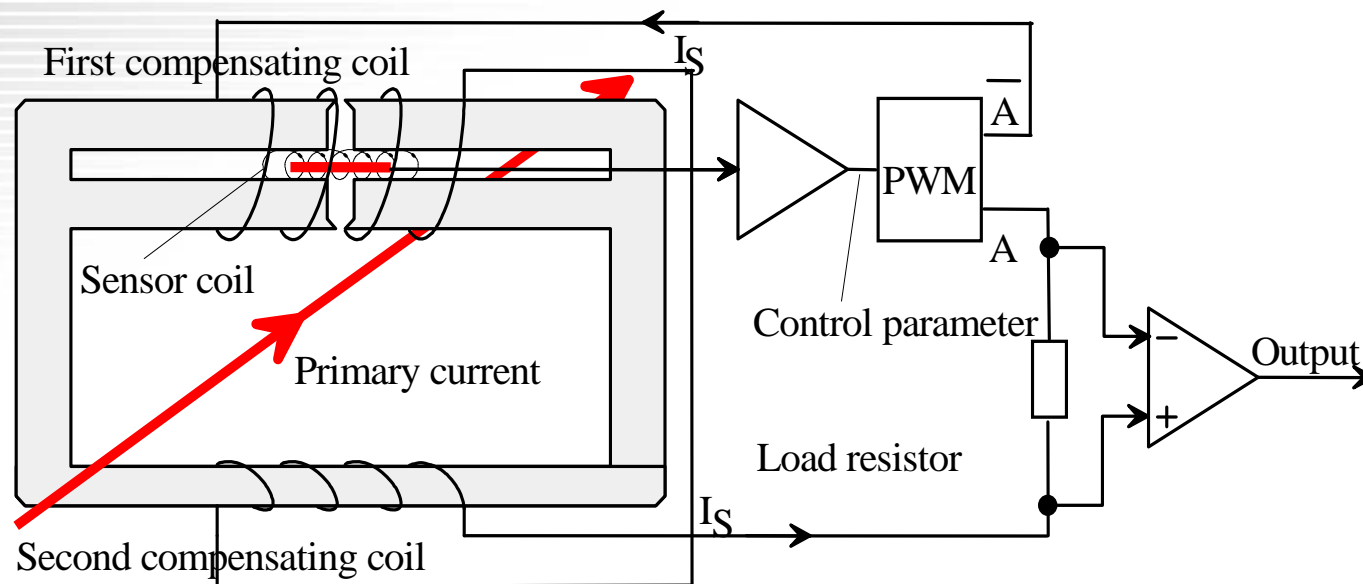




# Protection and supervisory functions

- ▶ interlock and dead time generation for TOP and BOTTOM IGBT
- ▶ short pulse suppression
- ▶ input pulse shaping
- ▶ input signal clamping
- ▶ under voltage monitoring of the (internal) supply voltage on primary side (SKiiP2/3) and secondary side (SKiiP3)
- ▶ transient over voltage and inverted polarity protection by suppressor diode
- ▶ ceramic substrate over temperature protection ( if forced air cooling is used)
- ▶ short circuit and over current protection
- ▶ Vcesat protection (SKiiP3)
- ▶ line to ground fault protection (only for type SKiiP2 GD, GH)
- ▶ over voltage protection of the DC link voltage (optional; SKiiP3 GD: standard)

# Compensated current sensor: working principle



Compared with Hall effect sensor

- No temperature dependence of the off-set
- Negligible offset failure

# SKiiP – Logistical Details

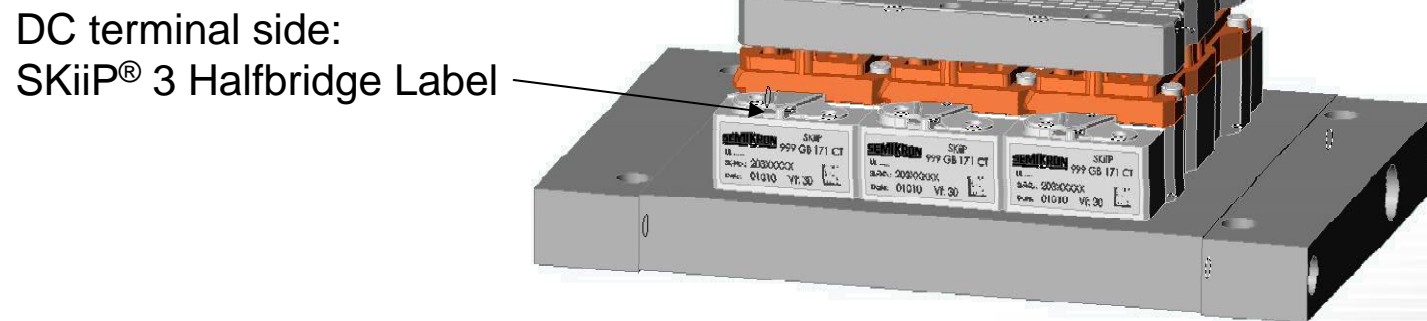
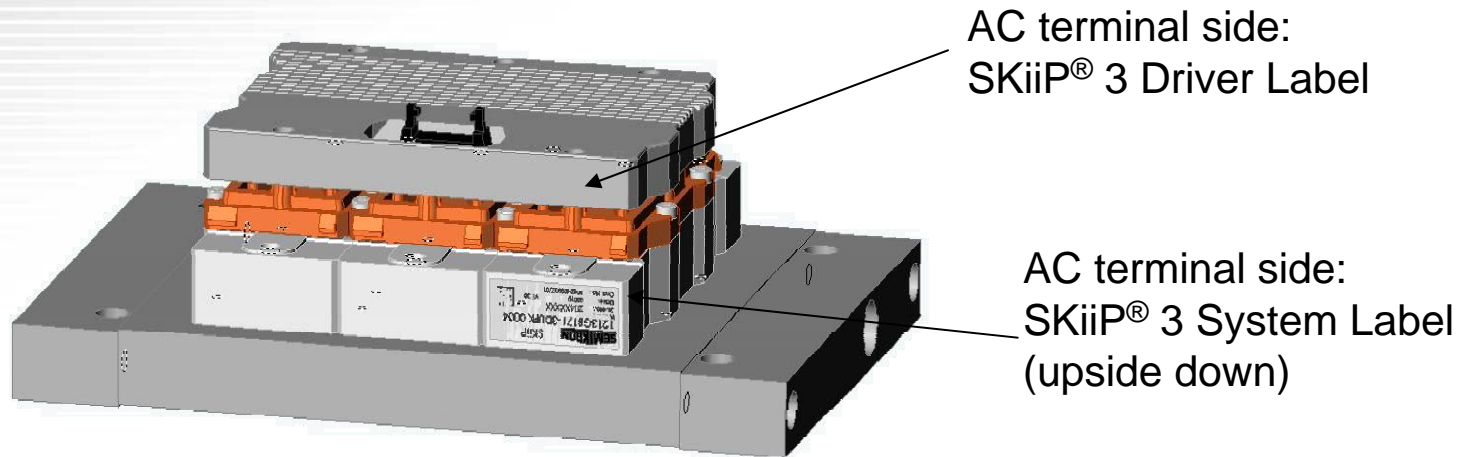
# SKiiP<sup>®</sup> 3 type designation system

SKiiP ①②③④⑤⑤⑥⑥⑦-⑧⑨⑨⑩

SKiiP3 example: SKiiP 5 1 3 G D 1 2 2 - 3 DU L

- ① nominal current  $I_C$  (@  $T_{\text{heatsink}}=25^\circ\text{C}$ ) divided by 100 as e.g. 500A →5, can contain 2 letters eg. 15,
- ② SKiiP3: insulation DBC (direct bonded copper) ceramic substrate type  
0 →standard aluminum nitride (AlN) DBC ceramic  
1 →standard aluminum oxide ( $\text{Al}_2\text{O}_3$ ) DBC ceramic
- ③ SKiiP generation , e.g. 3 for 3<sup>rd</sup> generation
- ④ chip type as e.g. G = IGBT
- ⑤ circuit     B →2 - pack (half bridge, dual) H →4 - pack ( single phase bridge)  
              D →6 - pack ( 3 phase bridge) DL →6 - pack + brake chopper
- ⑥ voltage class 12 → $V_{\text{CES}} = 1200 \text{ V}$  17 → $V_{\text{CES}} = 1700 \text{ V}$
- ⑦ chip generation
- ⑧ number of used modular half bridges (2-packs)
- ⑨ SKiiP3: gate drive designator  
DU →gate driver with DC-link voltage measurement and over voltage protection  
D →gate driver without DC-link voltage measurement  
DUF →gate driver with DC-link voltage measurement, over voltage protection and F-Option  
(optional for GB type only)  
DF →gate driver without DC-link voltage measurement and F-Option (optional for GB type only)
- ⑩ SKiiP3: heat sink designator L →standard profile for forced air cooling  
W →standard profile for liquid cooling, K →Customer specific heat sink

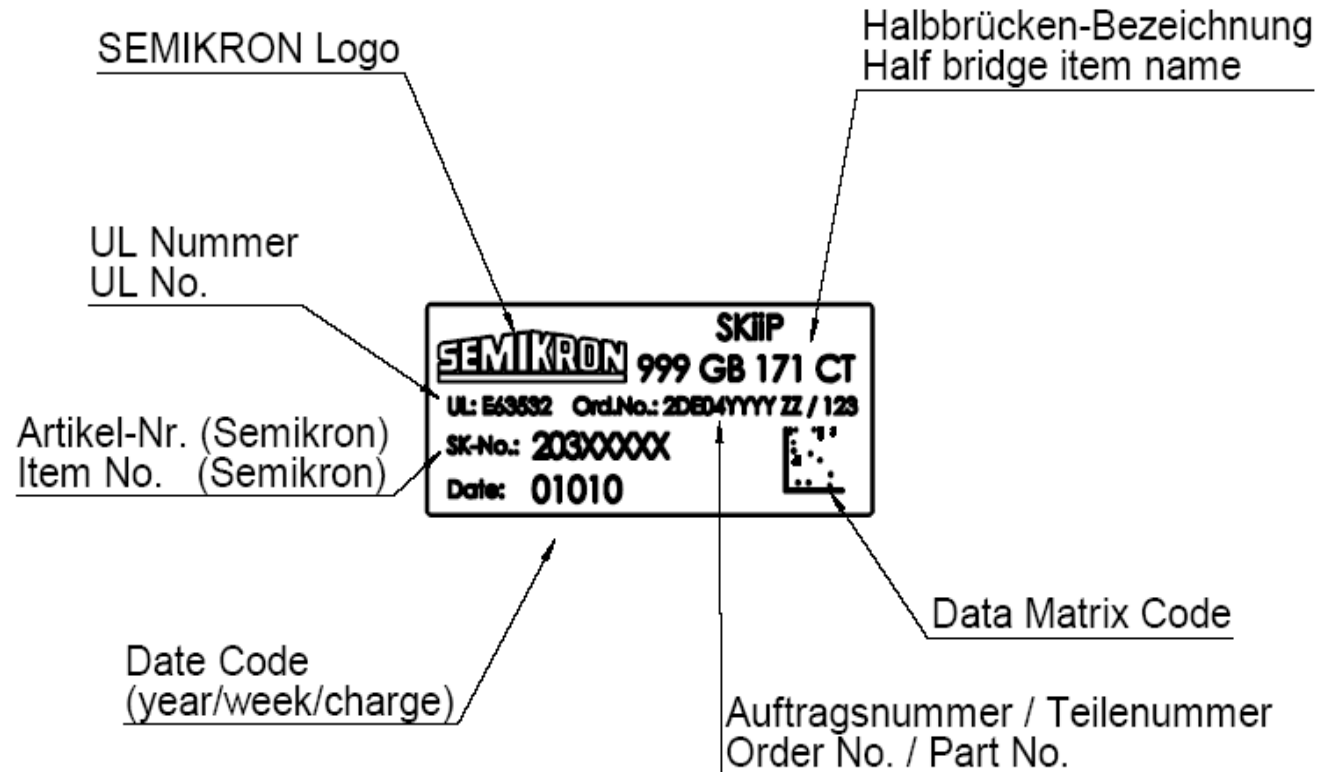
# position of SKiiP<sup>®</sup> 3 System and half bridge labels



## Identification (4): label SKiiP<sup>®</sup> 3



# Identification (1): label SKiiP<sup>®</sup> 3 Half Bridge

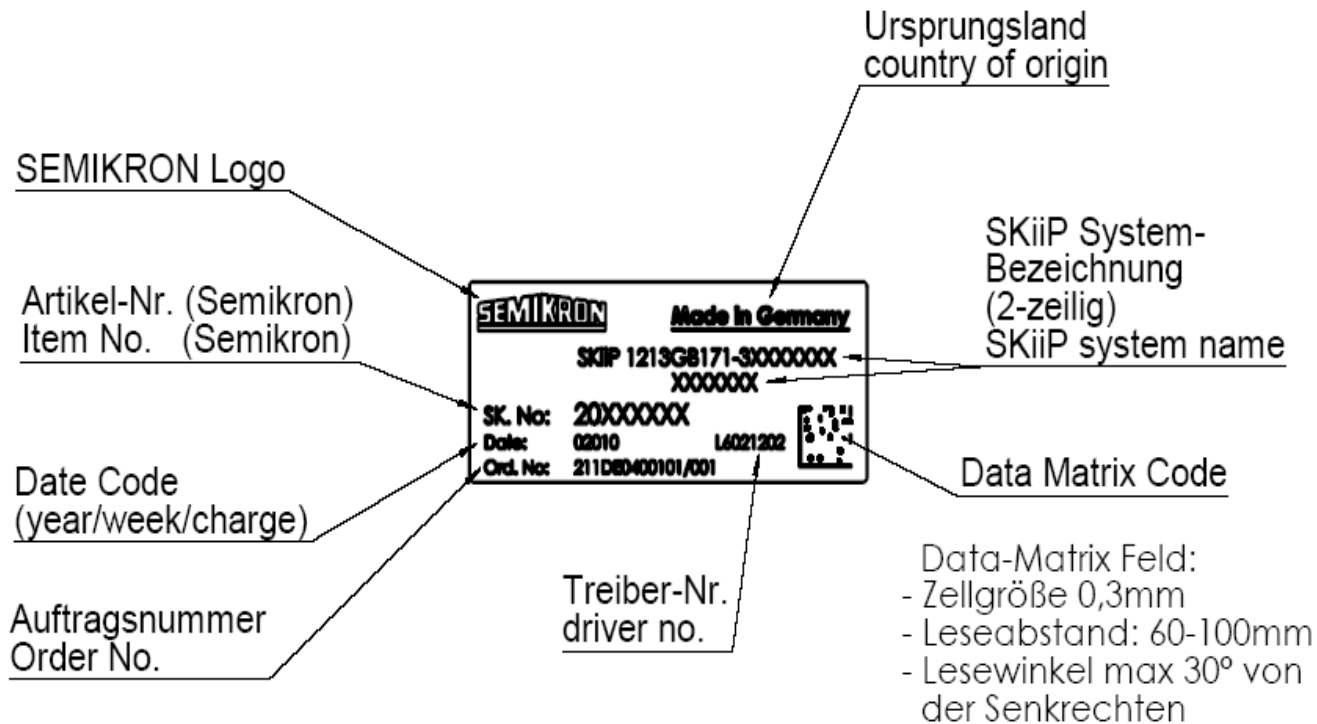


## Identification (4): label SKiiP<sup>®</sup> 3

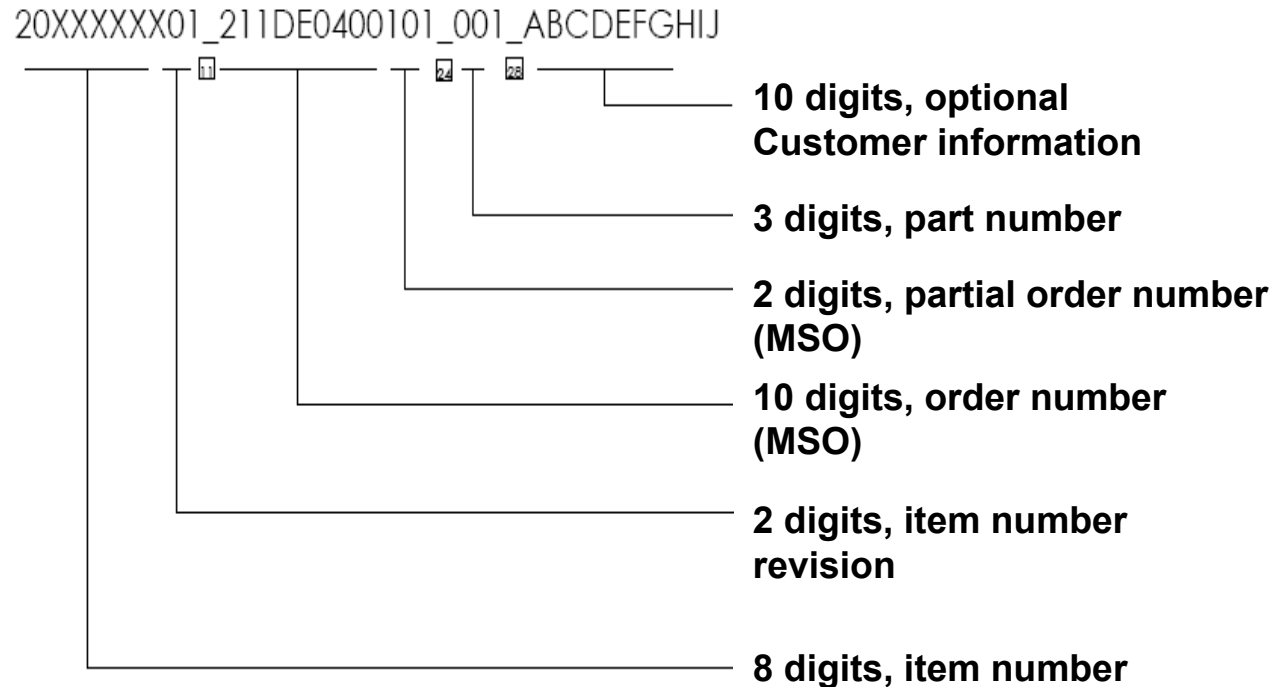




# Identification (1): label SKiiP® 3 System

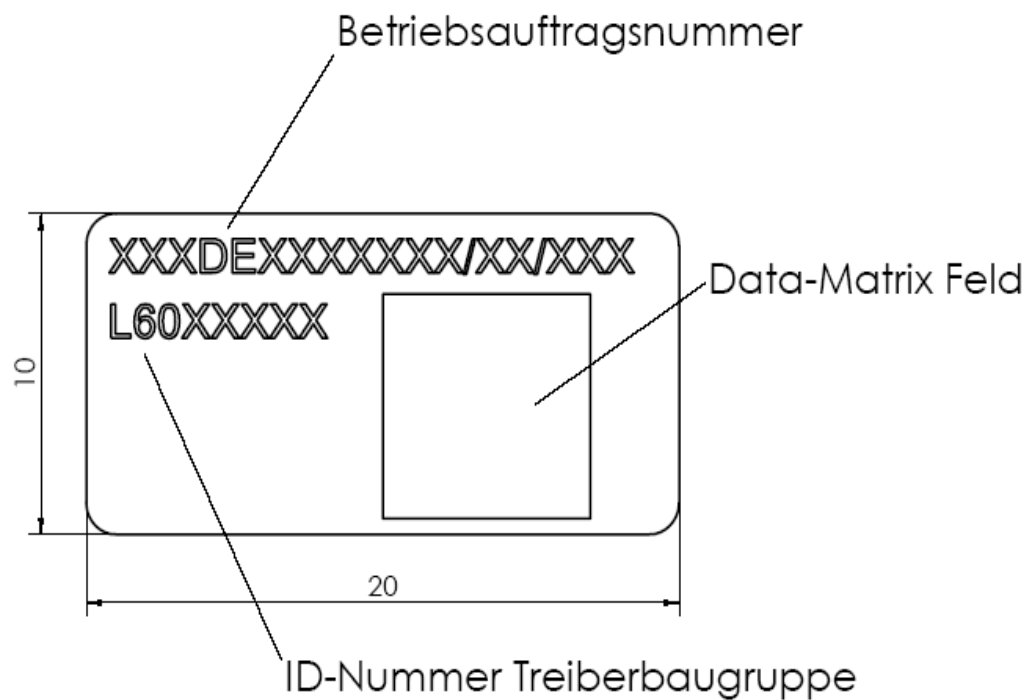


# Identification (2): label SKiiP<sup>®</sup> 3 Data Matrix Code



**Blanks on position 11; 24; 28**

# Label SKiiP<sup>®</sup> 3 Driver



# SKiiP<sup>®</sup> 3 Driver Label



# SKiiP® 3 Warranty Label



Please note:  
warranty is lost  
when cover  
is removed